Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application:

1 1. (Amended) A method of self-calibrating and testing the vaporized flow of 2 a liquid precursor in a thin film vaporization system comprising the steps of: 3 providing a thin film vaporization system comprising stored liquid precursors in 4 tanks under pressure connected to a deposition chamber via a manifold which in turn is 5 connected to pipe lines emanating from each tank and coupled to own liquid flow 6 meters (LFMs) and injection valves (IVs); 7 activating a servo mechanism to pump down said deposition chamber to achieve 8 partial vacuum therein; 9 opening a downstream throttle valve (TV) for a carrier gas to flow through said 10 manifold to commence self-calibration wherein said carrier gas is a second helium 11 carrier gas; a first timing to monitor a baseline self-calibrated pressure by a pre-determined 12 13 TV opening which correlates with the specified baseline pressure in said deposition 14 chamber; 15 a second timing to allow for the stabilization of carrier gas after throttling said TV 16 to a predetermined opening; 17 selecting a liquid precursor and its own said respective pipe line with said own 18 LFM and own IV connected to said deposition chamber via said manifold; 19 setting said own IV to a predetermined opening to start said liquid precursor to 20 flow;

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| 21 | setting said TV opening to a normal liquid precursor flow rate for film deposition; |
|----|---|
| 22 | a third timing to allow for liquid precursor flow to stabilize; |
| 23 | a fourth timing to allow vaporization of said liquid precursor in said deposition |
| 24 | chamber; |
| 25 | measuring final pressure in said deposition chamber; |
| 26 | stopping the flow of said precursor fluid; and |
| 27 | pumping down said deposition chamber to continue with said film deposition |
| 28 | pending the result of said pressure rise. |
| 1 | 2. (Original) The method according to claim 1, wherein said tanks are |
| 2 | pressurized by helium gas. |
| 1 | 3. (Original) The method according to claim 2, wherein said helium gas is |
| 2 | pressurized to between about 20 to 30 pounds per square inch gauge (psig). |
| 1 | 4. (Original) The method according to claim 1, wherein said helium gas is |
| 2 | kept at room temperature. |
| 1 | 5. (Original) The method according to claim 1, wherein said manifold has |
| 2 | heater elements. |
| 1 | 6. (Original) The method according to claim 5, wherein said heated fixture |
| 2 | elements are spaced nominally at 290 mils between about 250 to 350 mils from |
| 3 | distribution shower head. |
| 1 | 7. (Original) The method according to claim 5, wherein said heated fixture is |
| 2 | heated nominally to 400° C between about 350 to 450° C. |
| 1 | 8. (Canceled) |

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1 9. (Amended) The method according to claim 1, wherein flow of said second

helium carrier gas through said manifold is between about 750 to 850 milligrams per

3 minute (mgm).

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- 1 10. (Original) The method according to claim 1, wherein said first timing is
- 2 between about 5 to 15 seconds.
- 1 11. (Original) The method according to claim 1, wherein said baseline self-
- 2 calibrated pressure is between about 2 to 4 torr.
- 1 12. (Original) The method according to claim 1, wherein said second timing is
- 2 between about 4 to 6 seconds.
- 1 13. (Original) The method according to claim 1, wherein said liquid precursor
- 2 is tetraethylorthosilicate (TEOS).
- 1 14. (Original) The method according to claim 1, wherein said liquid precursor
- 2 is triethylborate (TEB).
- 1 15. (Original) The method according to claim 1, wherein said liquid precursor
- 2 is tri-ethylphosphate (TEPO).
- 1 16. (Original) The method according to claim 1, wherein said injection valve
- 2 (IV) comprises a venturi tube.
- 1 17. (Previously Presented) The method according to claim 1, wherein said
- 2 normal liquid precursor flow rate is between 800 to 1000 milligram per minute (mgm).
- 1 18. (Original) The method according to claim 1, wherein said third timing to
- 2 allow for liquid precursor to stabilize is between about 7 to 9 seconds.
- 1 19. (Original) The method according to claim 1, wherein said fourth timing to
- 2 allow for liquid precursor vaporized flow to be verified is between about 4 to 6 seconds.

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1 20. (Original) The method according to claim 1, wherein said final pressure in 2 said deposition chamber is between about 6.5 and 7.5 torr.

- 1 21. (Original) The method according to claim 1, wherein said pumping down
- 2 said deposition chamber is accomplished within between about 9 to 11 seconds.
- 1 22 31. (Canceled)